

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

2SA1358

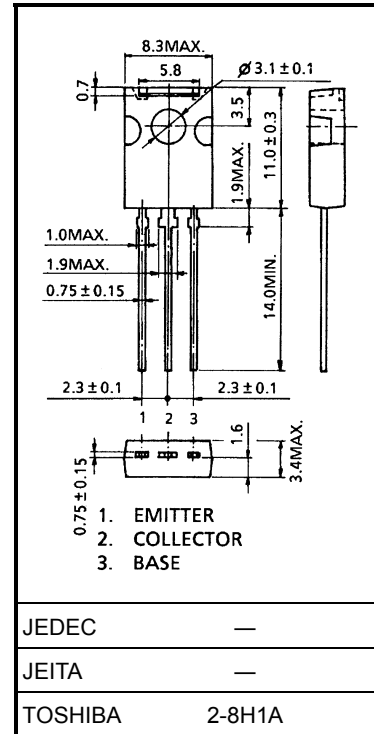
Audio Frequency Power Amplifier Applications

Unit: mm

- Complementary to 2SC3421
- Suitable for driver of 60 to 80 watts
- High breakdown voltage

Maximum Ratings (Tc = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-120	V
Collector-emitter voltage	V_{CE0}	-120	V
Emitter-base voltage	V_{EB0}	-5	V
Collector current	I_C	-1	A
Base current	I_B	-100	mA
Collector power dissipation	P_C	1.5	W
		10	
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55 to 150	°C

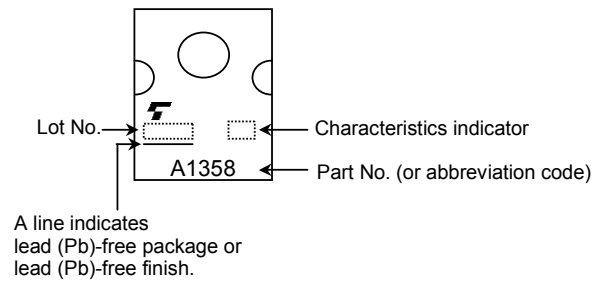


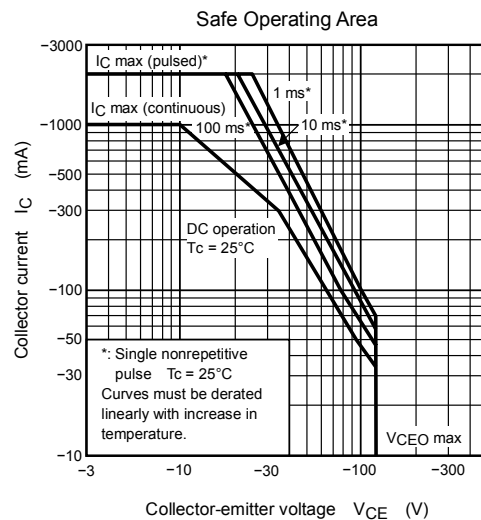
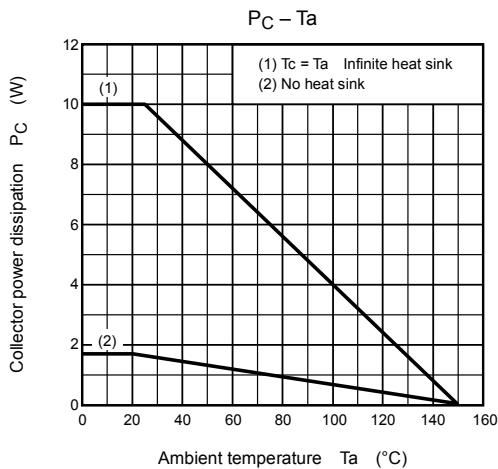
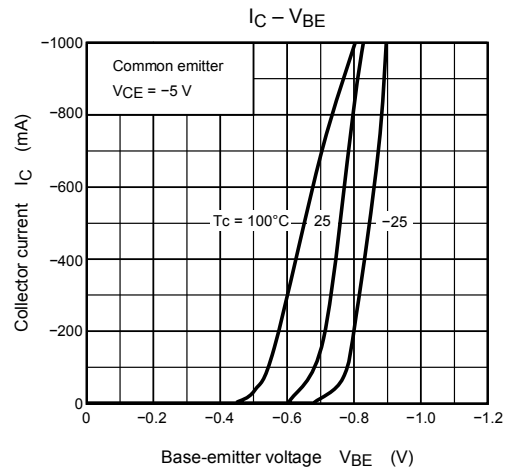
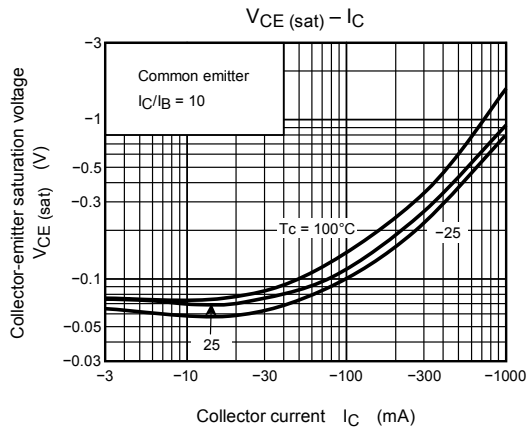
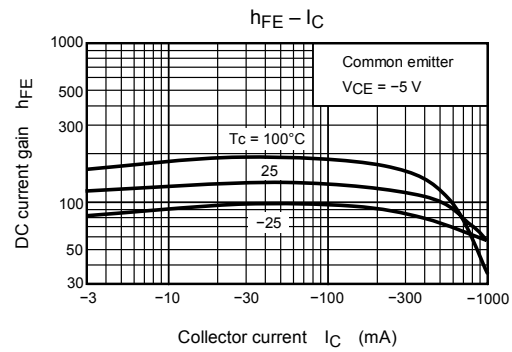
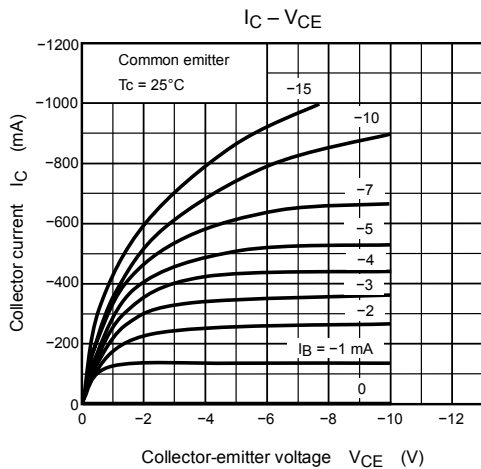
Electrical Characteristics (Tc = 25°C)

Weight: 0.82 g (typ.)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = -120\text{ V}, I_E = 0$	—	—	-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$	—	—	-100	nA
Collector-emitter breakdown voltage	$V_{(BR) CEO}$	$I_C = -10\text{ mA}, I_B = 0$	-120	—	—	V
Emitter-base breakdown voltage	$V_{(BR) EBO}$	$I_E = -1\text{ mA}, I_C = 0$	-5	—	—	V
DC current gain	h_{FE} (Note)	$V_{CE} = -5\text{ V}, I_C = -100\text{ mA}$	80	—	240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{ mA}, I_B = -50\text{ mA}$	—	-0.40	-1.0	V
Base-emitter voltage	V_{BE}	$V_{CE} = -5\text{ V}, I_C = -500\text{ mA}$	—	-0.77	-1.0	V
Transition frequency	f_T	$V_{CE} = -5\text{ V}, I_C = -100\text{ mA}$	—	120	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	30	—	pF

Note: h_{FE} classification O: 80 to 160, Y: 120 to 240

Marking



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